

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention

METHOD OF FORMING A LOW VOLTAGE GATE OXIDE
LAYER AND TUNNEL OXIDE LAYER IN AN EEPROM CELL

Application Number : 10/717149



Confirmation Number: 6780

First Named Applicant: Alan Renninger

Attorney Docket Number: ATM-262

Art Unit: 2818

Examiner:


Search string: (5882993 or 5254489).pn

Certification: This Information Disclosure Statement was submitted under the following conditions, which satisfies the requirement under 37 CFR 1.97(e). The filer certified:


That each item of information contained in the information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement.

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	5882993	1999-03-16	Gardner et al.	A1	438	591
	2	5254489	1993-10-19	Nakata	A1	437	40

Signature

Examiner Name	Date
	12/06/05